

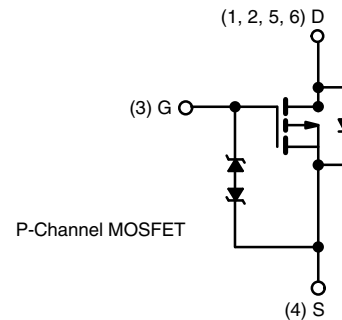
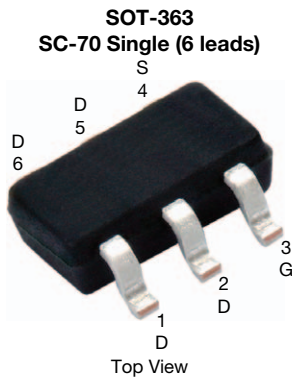
Automotive P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	-60
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.290
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.395
I_D (A)	-1.6
Configuration	Single
Package	SC-70

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Typical ESD protection: 800 V
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

Marking Code: 9B

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C ^a	-1.6
		$T_C = 125$ °C	-1
Continuous Source Current (Diode Conduction) ^a	I_S	-1.6	A
Pulsed Drain Current ^b	I_{DM}	-6.7	
Single Pulse Avalanche Current	I_{AS}	L = 0.1 mH	-8
Single Pulse Avalanche Energy			E_{AS}
Maximum Power Dissipation ^b	P_D	$T_C = 25$ °C	2.7
		$T_C = 125$ °C	0.5
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	125	°C/W
Junction-to-Foot (Drain)			

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA		-60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-1.5	-2.0	-2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V		-	-	± 5	μA
		V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 5	mA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -60 V	-	-	-1	μA
		V _{GS} = 0 V	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -60 V, T _J = 150 °C	-	-	-150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-5	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -2 A	-	0.230	0.290	Ω
		V _{GS} = -10 V	I _D = -2 A, T _J = 125 °C	-	-	0.470	
		V _{GS} = -10 V	I _D = -2 A, T _J = 150 °C	-	-	0.566	
		V _{GS} = -4.5 V	I _D = -1 A	-	0.305	0.395	
Forward Transconductance ^b	g _{fs}	V _{DS} = -10 V, I _D = -1.5 A		-	3	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = -25 V, f = 1 MHz	-	284	355	pF
Output Capacitance	C _{oss}			-	36	45	
Reverse Transfer Capacitance	C _{rss}			-	28	35	
Total Gate Charge ^c	Q _g	V _{GS} = -4.5 V	V _{DS} = -30 V, I _D = -1 A	-	3.6	5.4	nC
Gate-Source Charge ^c	Q _{gs}			-	1.2	-	
Gate-Drain Charge ^c	Q _{gd}			-	1.7	-	
Gate Resistance	R _g	f = 1 MHz		3.1	6.05	9	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = -30 V, R _L = 30 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _g = 1 Ω		-	44	66	ns
Rise Time ^c	t _r			-	25	38	
Turn-Off Delay Time ^c	t _{d(off)}			-	13	20	
Fall Time ^c	t _f			-	9	14	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	-6.7	A
Forward Voltage	V _{SD}	I _F = -0.5 A, V _{GS} = 0 V		-	-0.8	-1.2	V

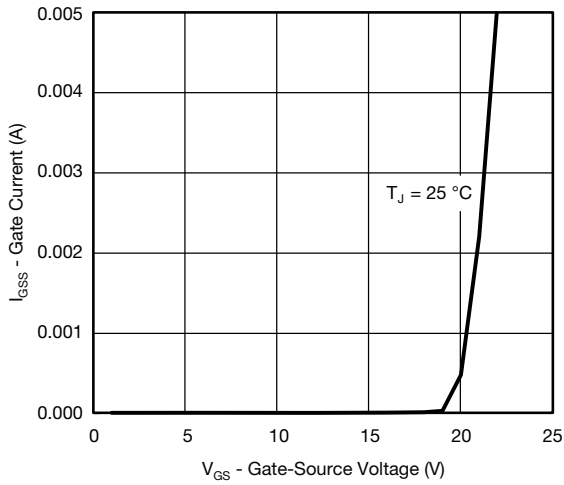
Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

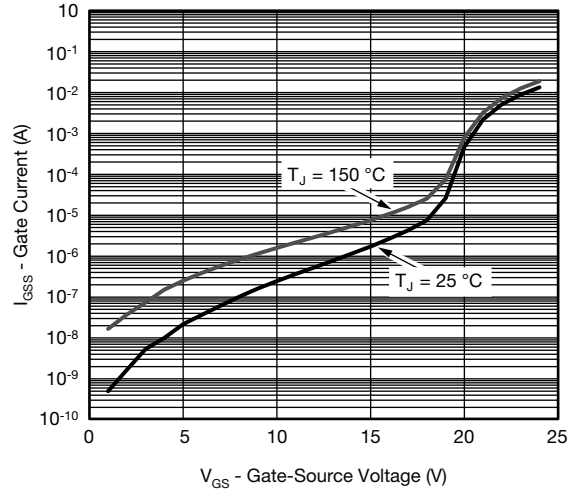
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



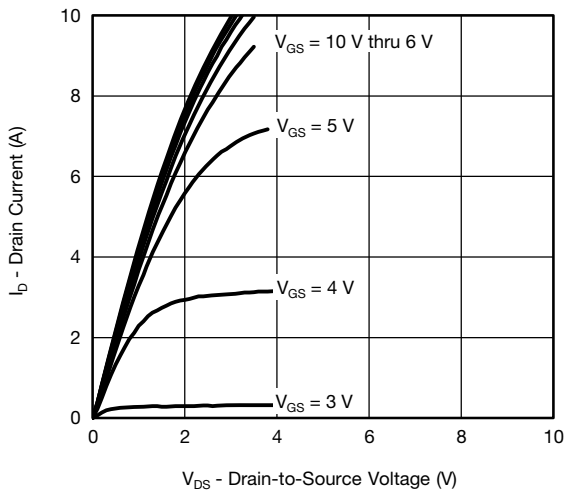
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



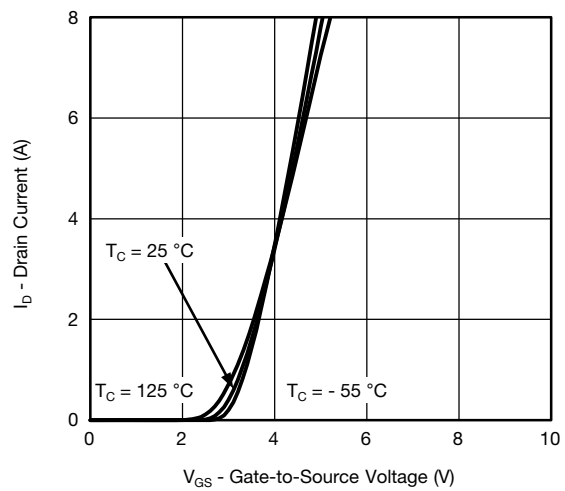
Gate Current vs. Gate-Source Voltage



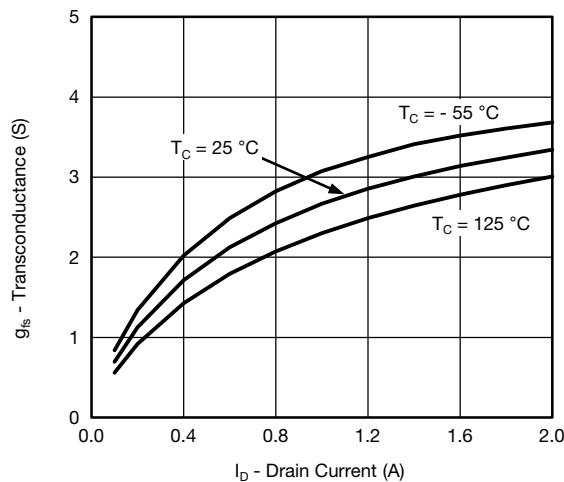
Gate Current vs. Gate-Source Voltage



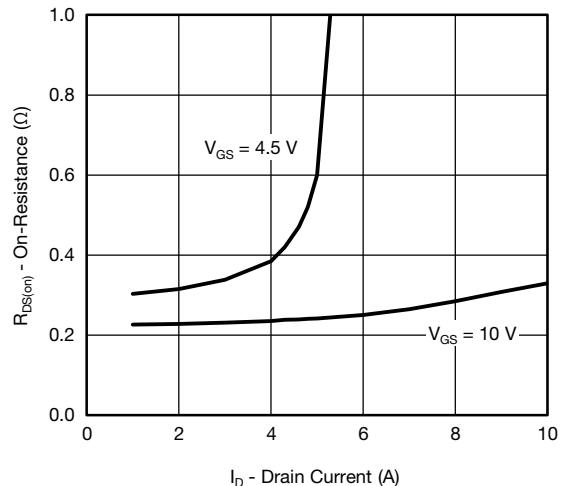
Output Characteristics



Transfer Characteristics



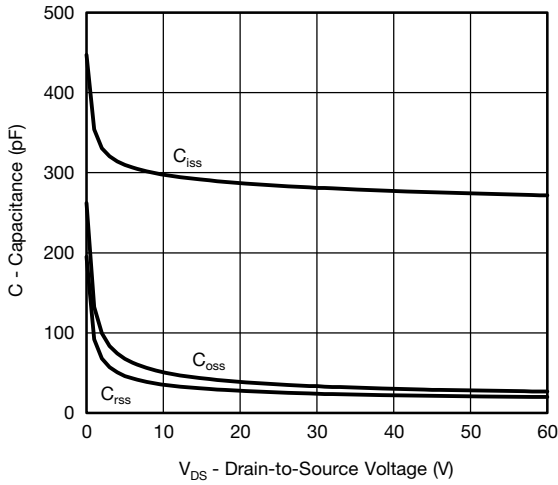
Transconductance



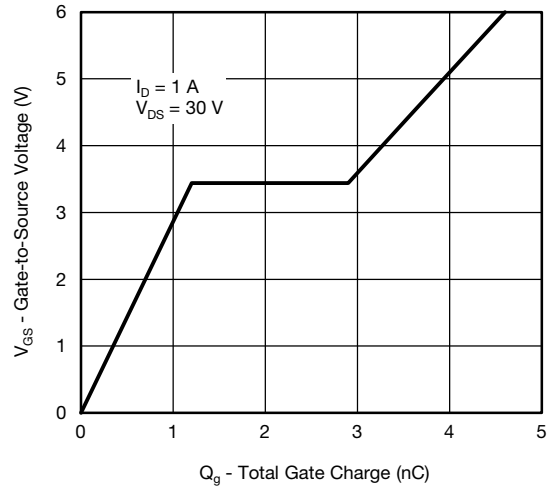
On-Resistance vs. Drain Current



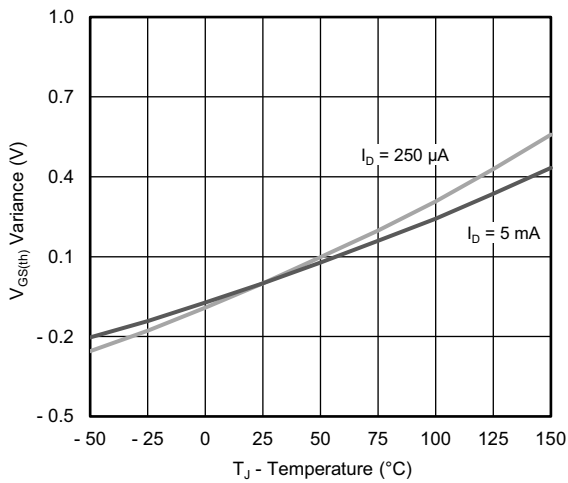
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



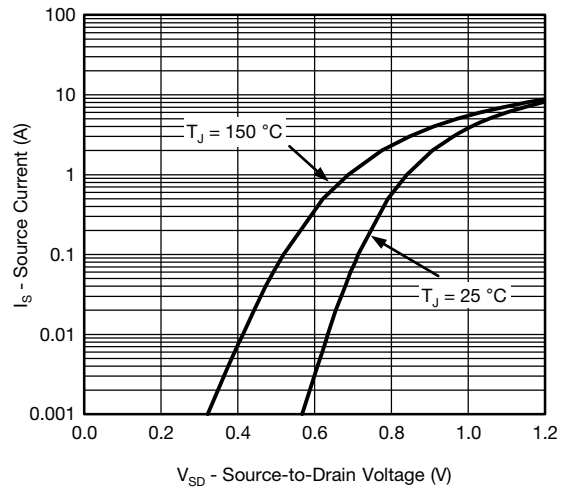
Capacitance



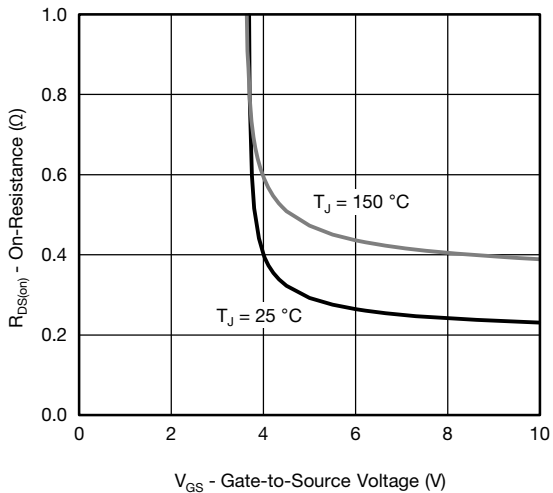
Gate Charge



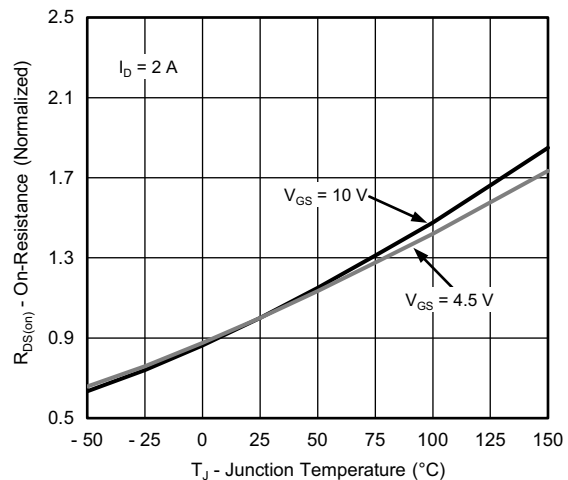
Threshold Voltage



Source Drain Diode Forward Voltage



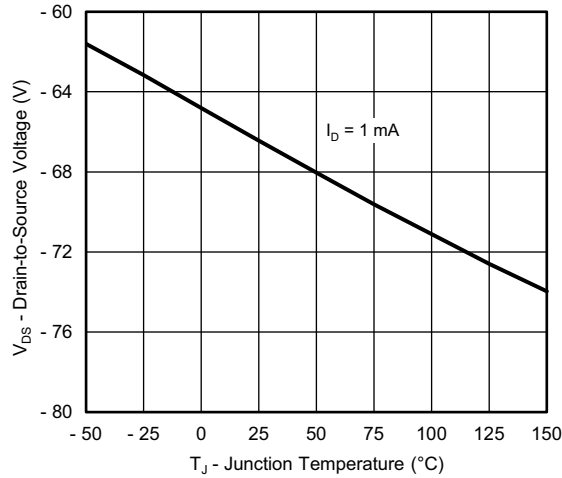
On-Resistance vs. Gate-to-Source Voltage



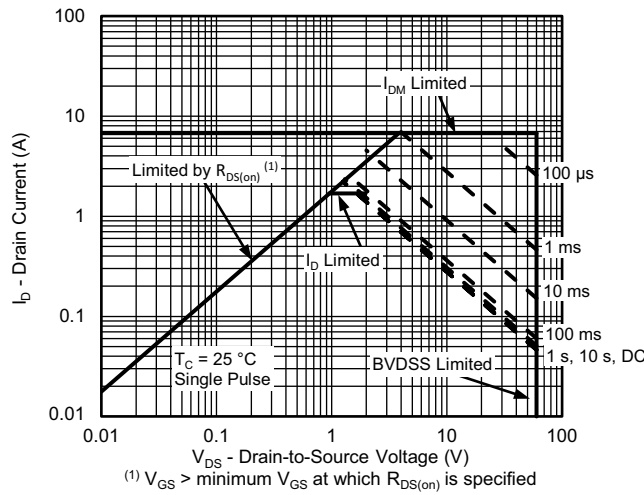
On-Resistance vs. Junction Temperature



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

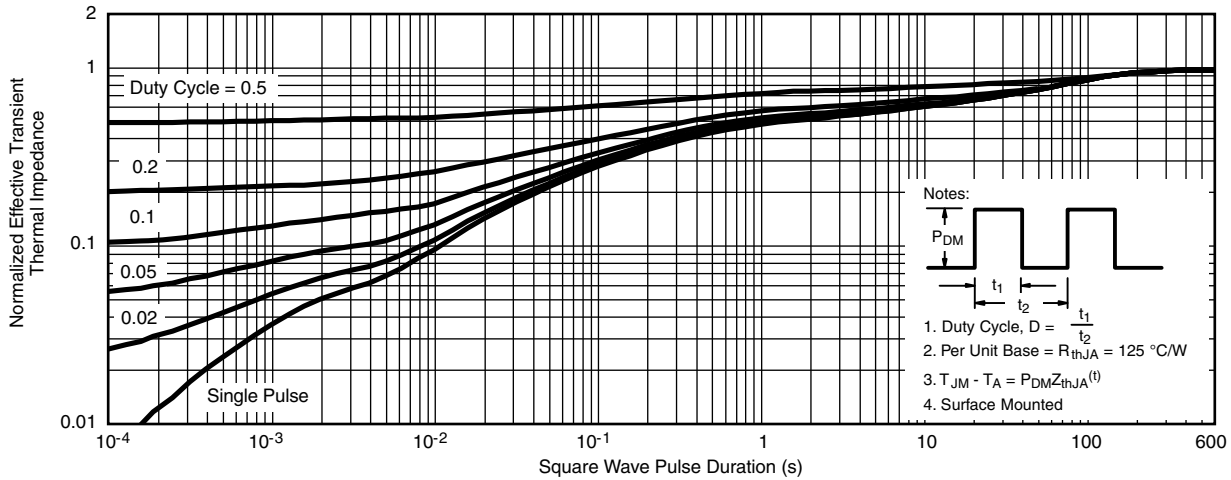


Drain Source Breakdown vs. Junction Temperature

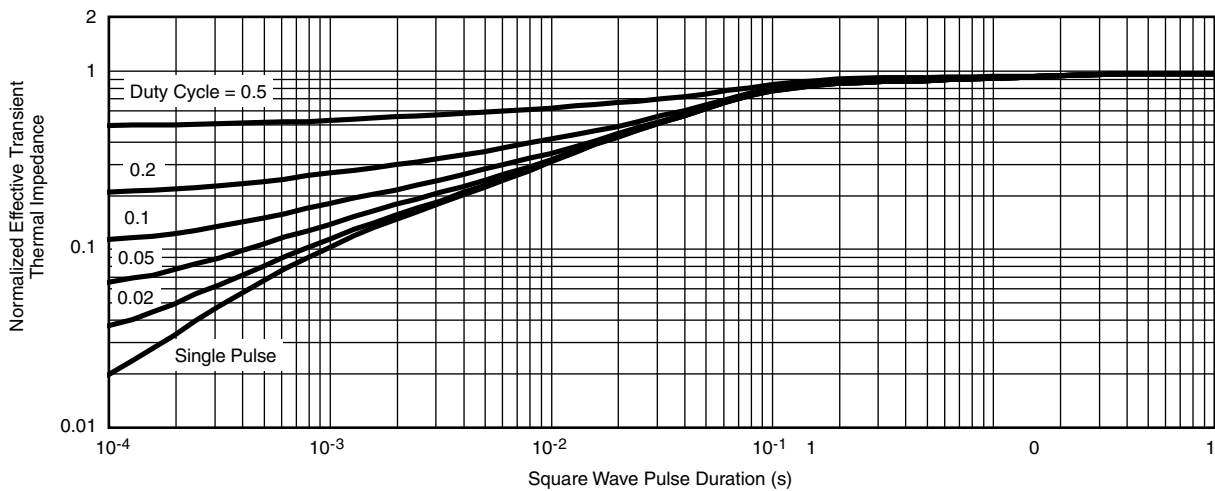




THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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SC-70

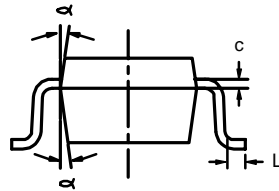
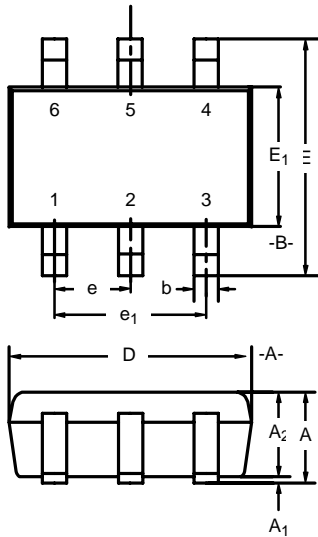
Ordering codes for the SQ rugged series power MOSFETs in the SC-70 package:

DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE
SQ1421EDH	-	SQ1421EDH-T1_GE3
SQ1431EH	SQ1431EH-T1-GE3	SQ1431EH-T1_GE3
SQ1440EH	-	SQ1440EH-T1_GE3
SQ1470AEH	-	SQ1470AEH-T1_GE3
SQ1539EH	-	SQ1539EH-T1_GE3
SQ1563AEH	-	SQ1563AEH-T1_GE3
SQ1902AEL	-	SQ1902AEL-T1_GE3
SQ1912AEEH	-	SQ1912AEEH-T1_GE3
SQ1912EH	-	SQ1912EH-T1_GE3

Note

a. Old ordering code is obsolete and no longer valid for new orders

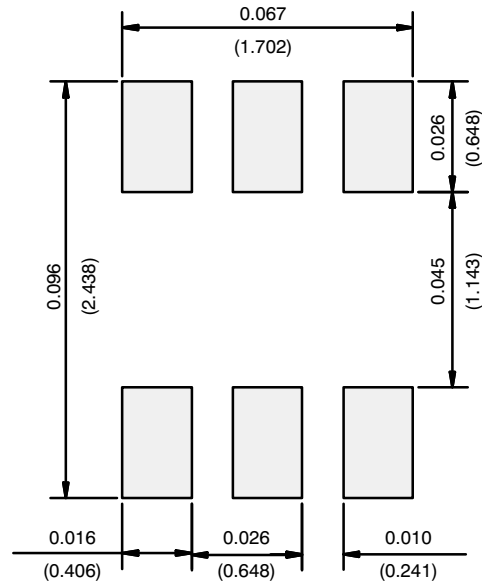
SC-70: 6-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	-	1.10	0.035	-	0.043
A ₁	-	-	0.10	-	-	0.004
A ₂	0.80	-	1.00	0.031	-	0.039
b	0.15	-	0.30	0.006	-	0.012
c	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		

ECN: S-03946—Rev. B, 09-Jul-01
DWG: 5550

RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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